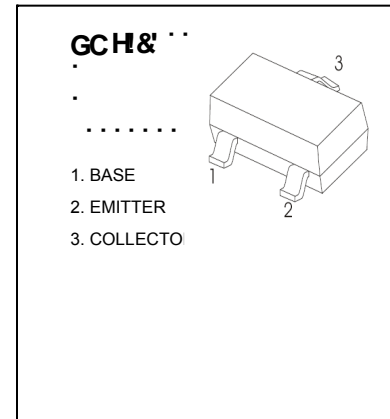


SOT-23 Plastic-Encapsulate Transistors

.....67, %± TRANSISTOR (NPN)



: 95HI F9G

- For general AF applications
- High collector current
- High current gain
- Low collector-emitter saturation voltage
- Complementary types: BC807 (PNP)

A5L-AI A F5HB; Gfh1&) °C i b`Ygg`cH Yfk JgY`bcHXL`

Gna Vc`	DUFUa YHf`	JUi Y`	I b]h
J76c`	Collector-Base Voltage	50	V
J79c`	Collector-Emitter Voltage	45	V
J96c`	Emitter-Base Voltage	5	V
7`	Collector Current -Continuous	0.5	A
D7`	Collector Power Dissipation	0.3	W
H^	Junction Temperature	150	°C
Hgfj`	Storage Temperature	-55-150	°C

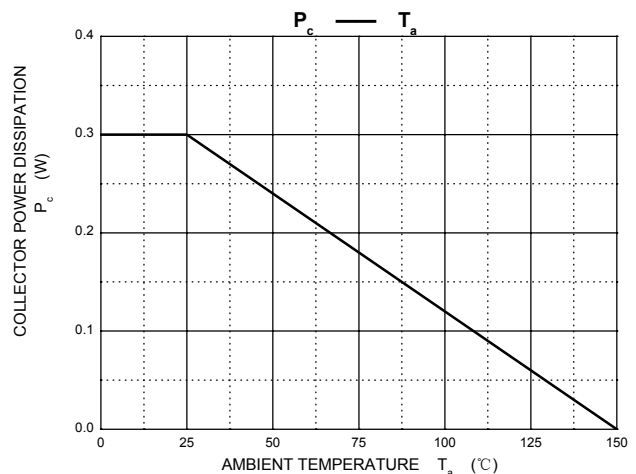
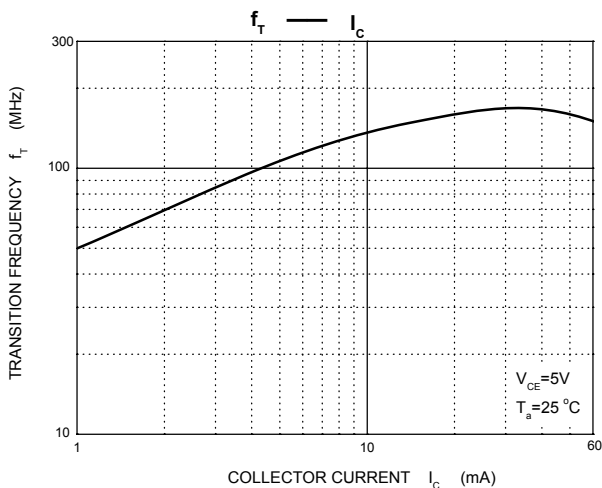
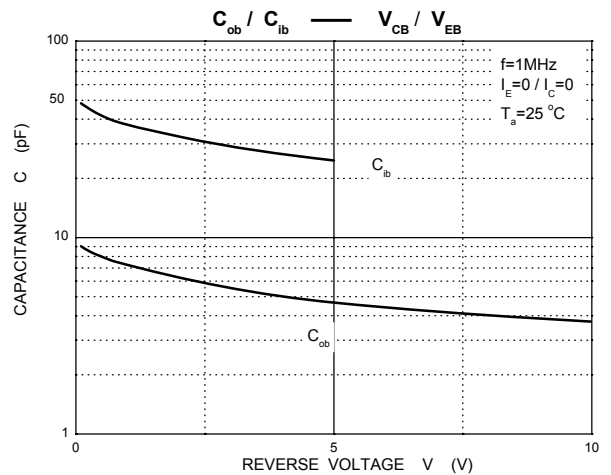
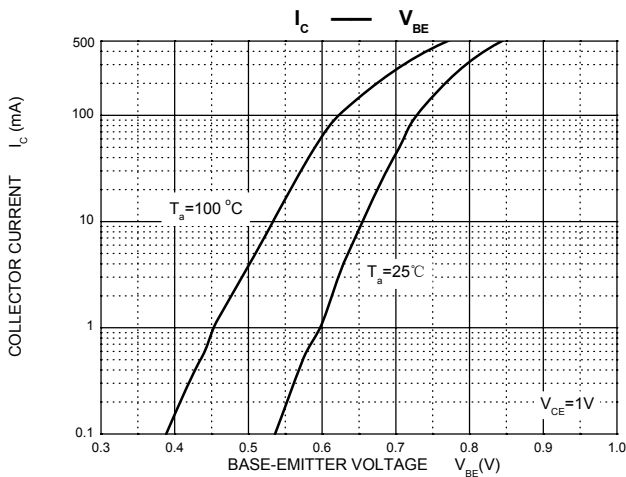
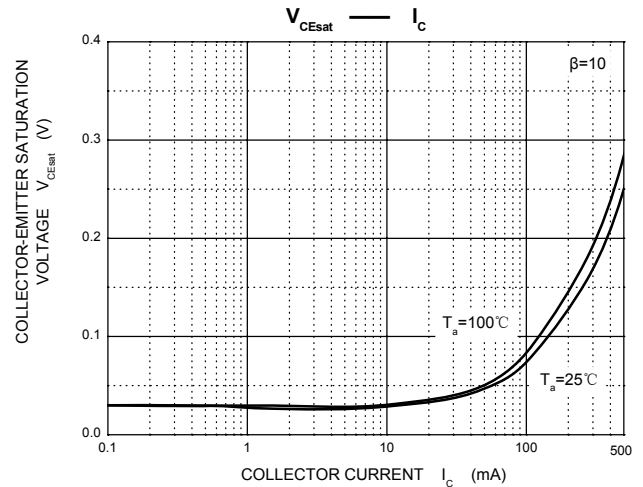
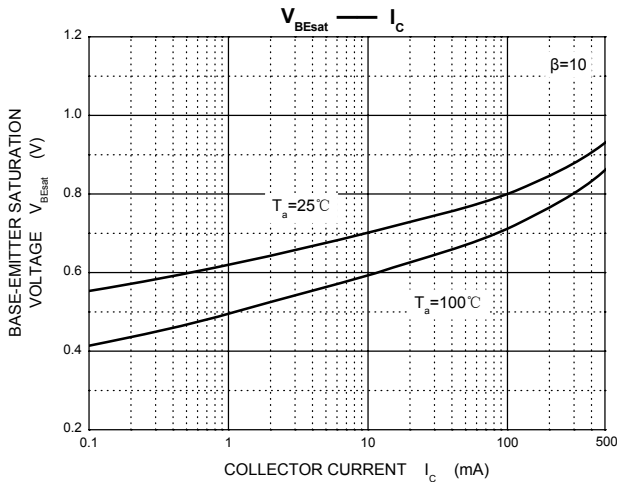
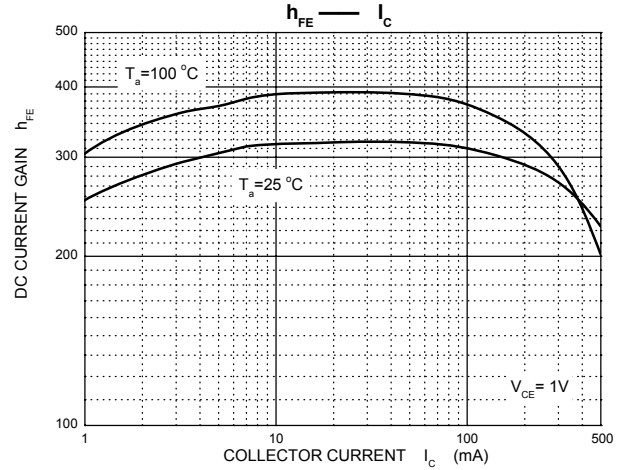
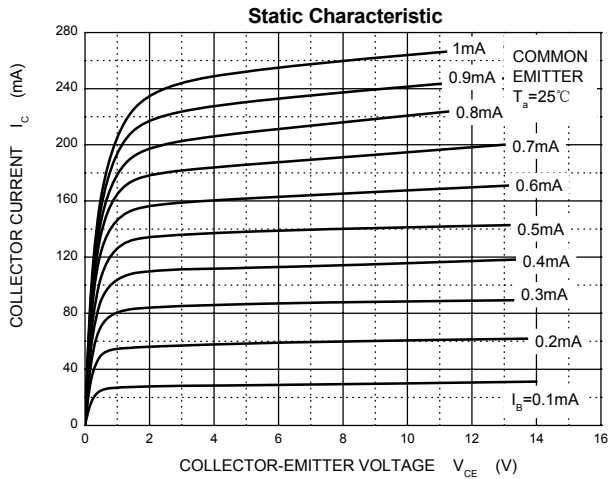
9 @7 HF 7 5 @7 < 5 F 5 7 H9F -GH7 G`fh1&) °C i b`Ygg`cH Yfk JgY`gdYWZ`YXL`

DUFUa YHf`	Gna Vc`	HYgh VtbX]hcbg`	Ain	Typ`	Aax	Unit
7c`YWcf!VUgY VfyU_Xck b`j`c`HJ` Y`	V <sub>CB0</sub>	I <sub>C</sub> = 10μA, I <sub>E</sub> =0	50			V
7c`YWcf!Ya ]Hf`VfyU_Xck b`j`c`HJ` Y`	V <sub>CE0</sub>	I <sub>C</sub> = 10mA, I <sub>B</sub> =0	45			V
9a ]Hf`!VUgY VfyU_Xck b`j`c`HJ` Y`	V <sub>EBO</sub>	I <sub>E</sub> = 1μA, I <sub>C</sub> =0	5			V
7c`YWcf`W HcZZW ffYbh	I <sub>CB0</sub>	V <sub>CB</sub> = 45 V, I <sub>E</sub> =0			0.1	μA
9a ]Hf`W HcZZW ffYbh	I <sub>EBO</sub>	V <sub>EB</sub> = 4V, I <sub>C</sub> =0			0.1	μA
87`W ffYbh] Ujb`.....	h <sub>FE(1)</sub>	V <sub>CE</sub> = 1V, I <sub>C</sub> = 100mA	100		600	
	h <sub>FE(2)</sub>	V <sub>CE</sub> = 1V, I <sub>C</sub> = 500mA	40			
7c`YWcf!Ya ]Hf`gUhi fU]cb`j`c`HJ` Y`	V <sub>CE(sat)</sub>	I <sub>C</sub> = 500mA, I <sub>B</sub> = 50mA			0.7	V
6 UgY!Ya ]Hf`gUhi fU]cb`j`c`HJ` Y`	V <sub>BE(sat)</sub>	I <sub>C</sub> = 500mA, I <sub>B</sub> = 50mA			1.2	V
6 UgY!Ya ]Hf`j`c`HJ` Y`	V <sub>BE</sub>	V <sub>CE</sub> = 1 V, I <sub>C</sub> = 500mA			1.2	V
7c`YWyf`VUdUW]UbW`	C <sub>ob</sub>	V <sub>CB</sub> =10V, f=1MHz		10		pF
HfUbg]hcb`Z`Yei`YbWni	f <sub>T</sub>	V <sub>CE</sub> = 5 V, I <sub>C</sub> = 10mA f=100MHz	100			MHz

7 @ GG= 7 5 HCB`C: `h<sub>FE`%</sub>

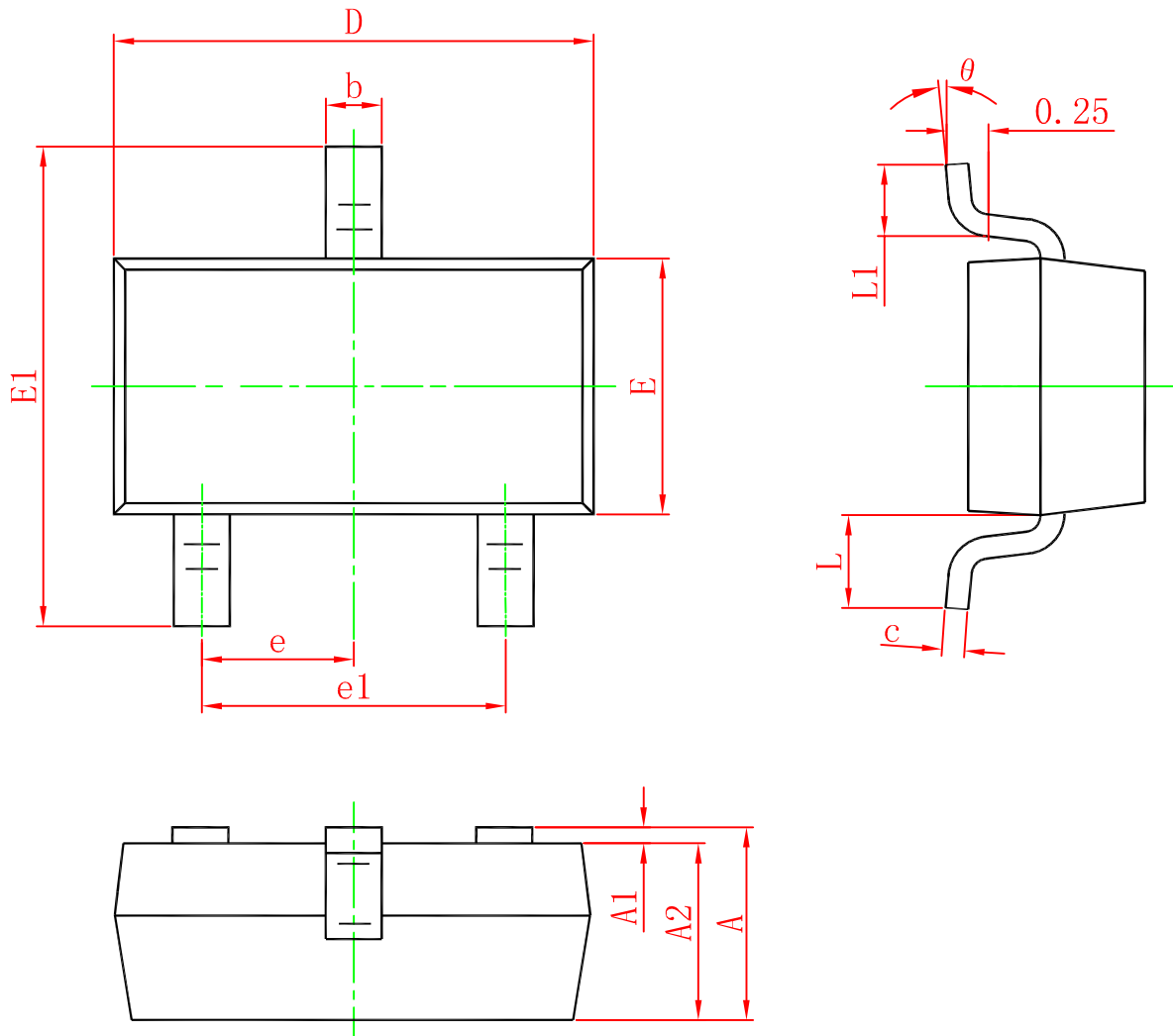
FUb`	67, %±!%`	67, %±!&`	67, %±!( \$`
FUb] Y`	%%\$!& \$`	% \$!( \$ \$`	&) \$!* \$ \$`
AUf_]b[ `	* 5`	* 6`	* 7`

# SOT-23 Plastic-Encapsulate Transistors



SOT-23 Plastic-Encapsulate Transistors

SOT-23 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°